

2SJ160, 2SJ161, 2SJ162

Silicon P Channel MOS FET

REJ03G0847-0200
(Previous: ADE-208-1182)

Rev.2.00

Sep 07, 2005

Description

Low frequency power amplifier

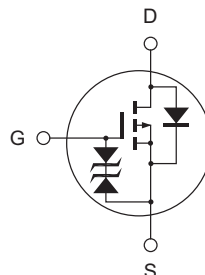
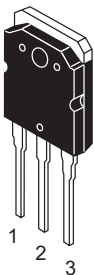
Complementary pair with 2SK1056, 2SK1057 and 2SK1058

Features

- Good frequency characteristic
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes
- Suitable for audio power amplifier

Outline

RENESAS Package code: PRSS0004ZE-A
(Package name: TO-3P)



1. Gate
2. Source (Flange)
3. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	2SJ160	-120	V
	2SJ161	-140	
	2SJ162	-160	
Gate to source voltage	V _{GSS}	±15	V
Drain current	I _D	-7	A
Body to drain diode reverse drain current	I _{DR}	-7	A
Channel dissipation	P _{ch} ^{Note 1}	100	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note: 1. Value at Tc = 25°C

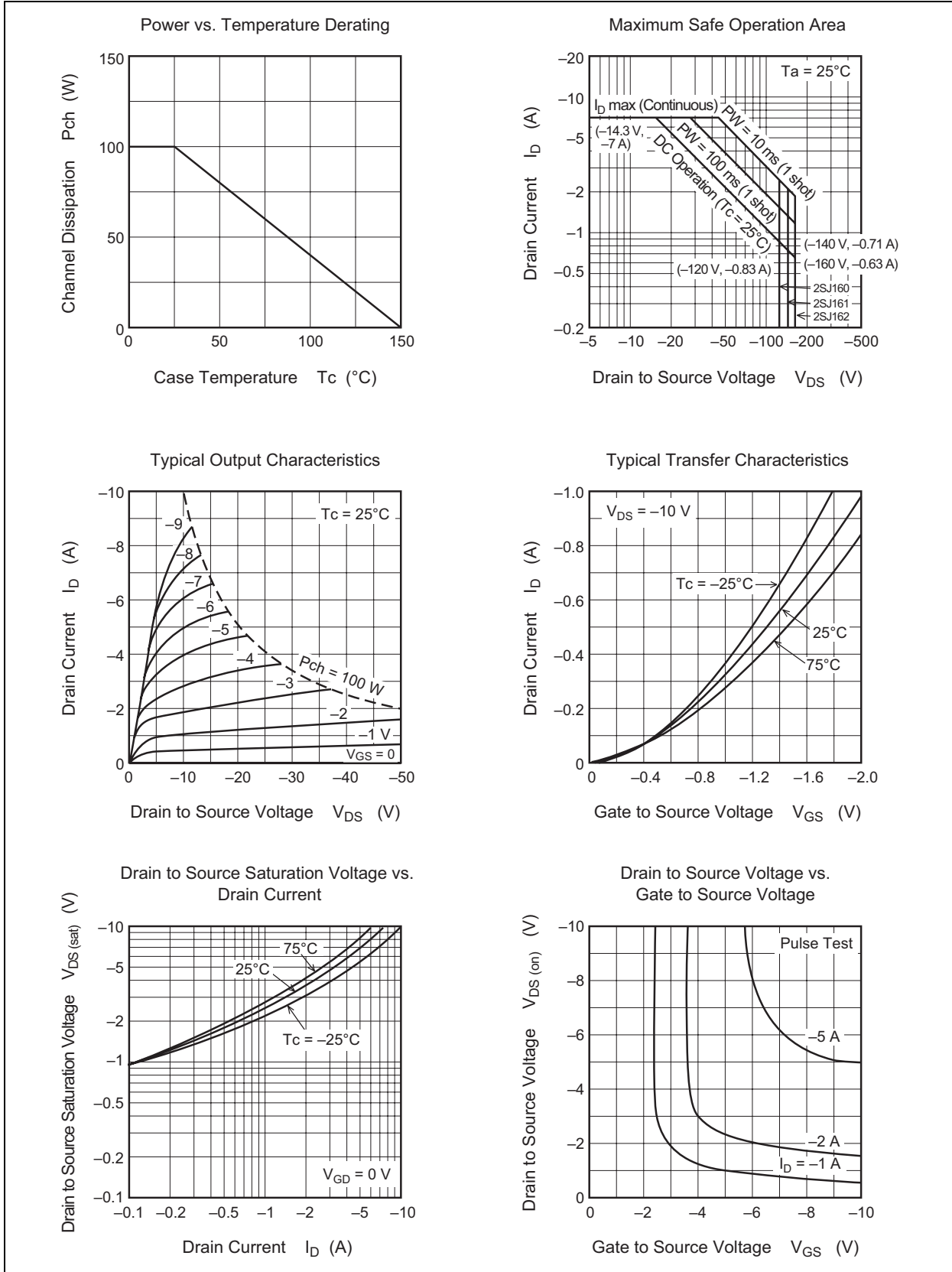
Electrical Characteristics

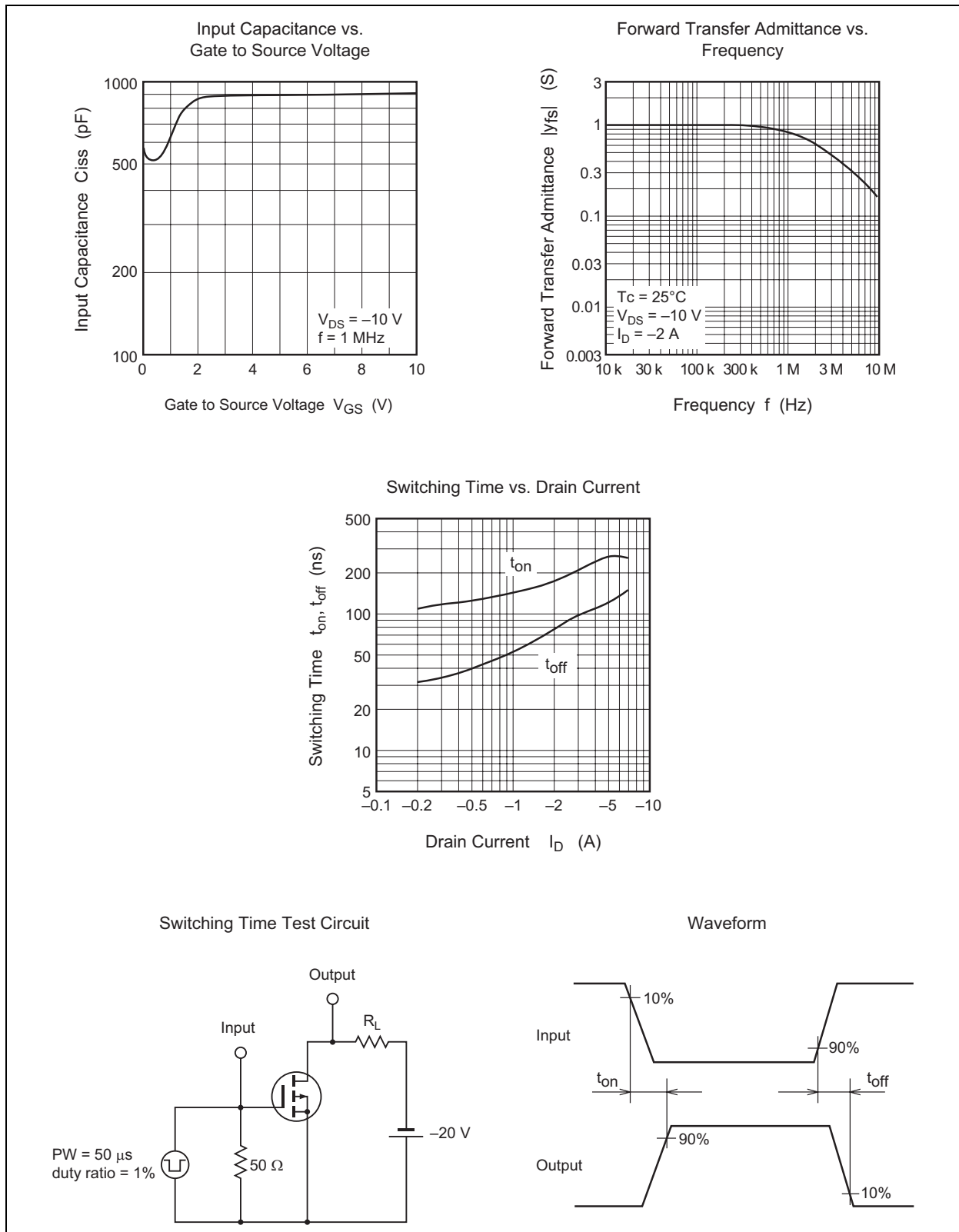
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	2SJ160	-120	—	—	V	I _D = -10 mA, V _{GS} = 10 V
	2SJ161	-140	—	—	V	
	2SJ162	-160	—	—	V	
Gate to source breakdown voltage	V _{(BR) GSS}	±15	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source cutoff voltage	V _{GS (off)}	-0.15	—	-1.45	V	I _D = -100 mA, V _{DS} = -10 V
Drain to source saturation voltage	V _{DS (sat)}	—	—	-12	V	I _D = -7 A, V _{GS} = 0 ^{Note 2}
Forward transfer admittance	y _{fs}	0.7	1.0	1.4	S	I _D = -3 A, V _{DS} = -10 V ^{Note 2}
Input capacitance	C _{iss}	—	900	—	pF	V _{GS} = 5 V, V _{DS} = -10 V, f = 1 MHz
Output capacitance	C _{oss}	—	400	—	pF	
Reverse transfer capacitance	C _{rss}	—	40	—	pF	
Turn-on time	t _{on}	—	230	—	ns	V _{DD} = -20 V I _D = -4 A
Turn-off time	t _{off}	—	110	—	ns	

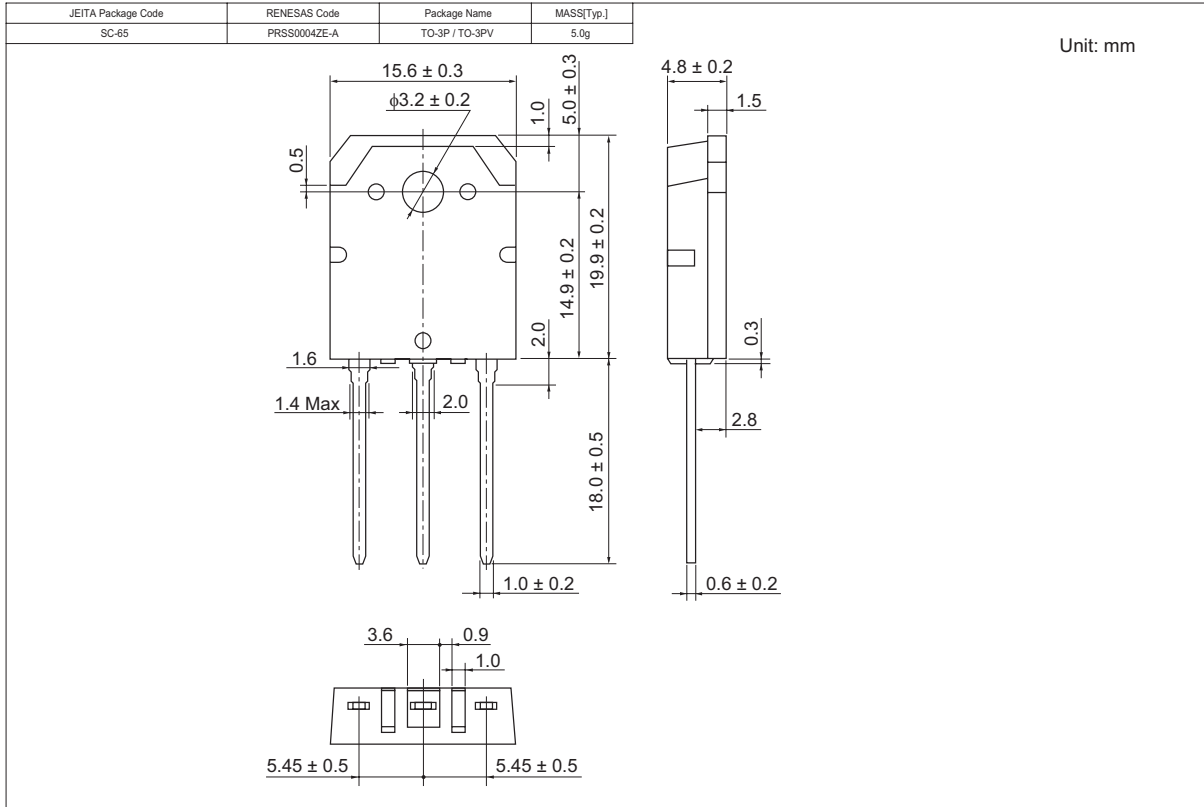
Note: 2. Pulse test

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SJ160-E	360 pcs	Box (Tube)
2SJ161-E	360 pcs	Box (Tube)
2SJ162-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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